P-channel Enhancement Mode Power MOSFET

Features

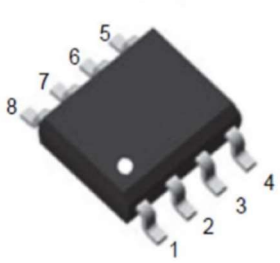
- VDS= -30V, ID= -9A
  RDS(ON) < 16 mΩ @ VGS = -10V
  RDS(ON) < 23 mΩ @ VGS = -4.5V

General Features

- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- Lead Free and Green Available

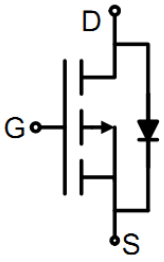
100% UIS TESTED!
100% ΔVds TESTED!

RoHS



SOP-8

pin assignment



Schematic diagram

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted			
Parameter	**Symbol**	**Value**	**Unit**
Drain-Source Voltage	V_{DS}	-30	V
Continuous Drain Current	I_D	-9	A
Pulsed Drain Current (note1)	I_{DM}	-36	A
Gate-Source Voltage	V_{GS}	±20	V
Power Dissipation	P_D	2.7	W
Single Pulse Avalanche Energy (note3)	EAS	231	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	ºC

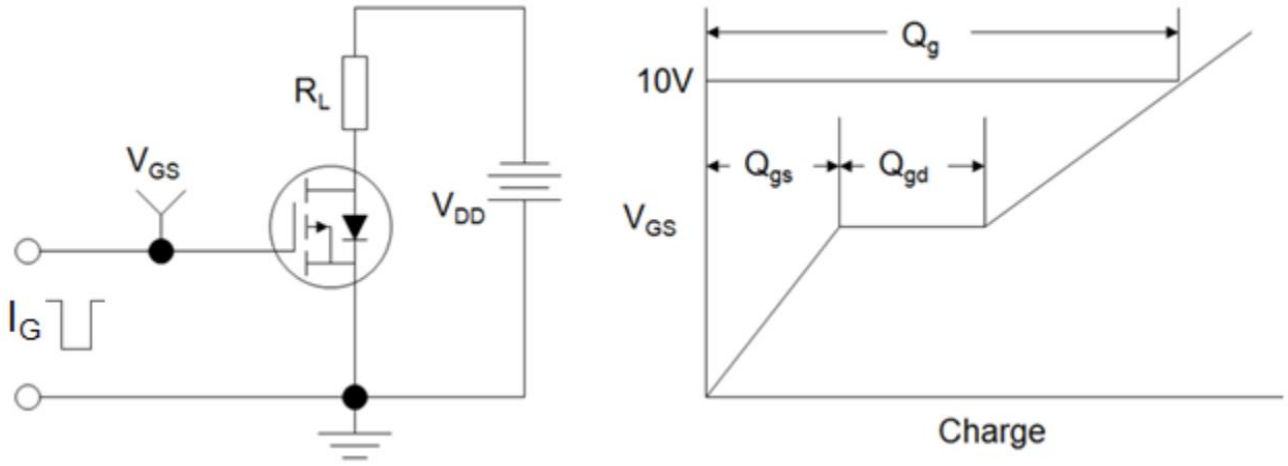
Thermal Resistance			
Parameter	**Symbol**	**Value**	**Unit**
Thermal Resistance, Junction-to-Ambient	R_{thJA}	47	ºC/W

Specifications T_J = 25ºC, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30V, V_{GS} = 0V	--	--	-1	uA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1		-3	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -3A	--		16	mΩ
		V_{GS} = -4.5V, I_D = -2A	--		23	
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1.0MHz	--	1253	--	pF
Output Capacitance	C_{oss}		--	181	--	
Reverse Transfer Capacitance	C_{rss}		--	158	--	
Total Gate Charge	Q_g	V_{DD} = -15V, I_D = -3A, V_{GS} = -10V	--	24.5	--	nC
Gate-Source Charge	Q_{gs}		--	3	--	
Gate-Drain Charge	Q_{gd}		--	6	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -15V, I_D = -3A, R_G = 1Ω	--	8	--	ns
Turn-on Rise Time	t_r		--	9	--	
Turn-off Delay Time	$t_{d(off)}$		--	26	--	
Turn-off Fall Time	t_f		--	8	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	-9	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = -3A, V_{GS} = 0V	--	--	-1.2	V

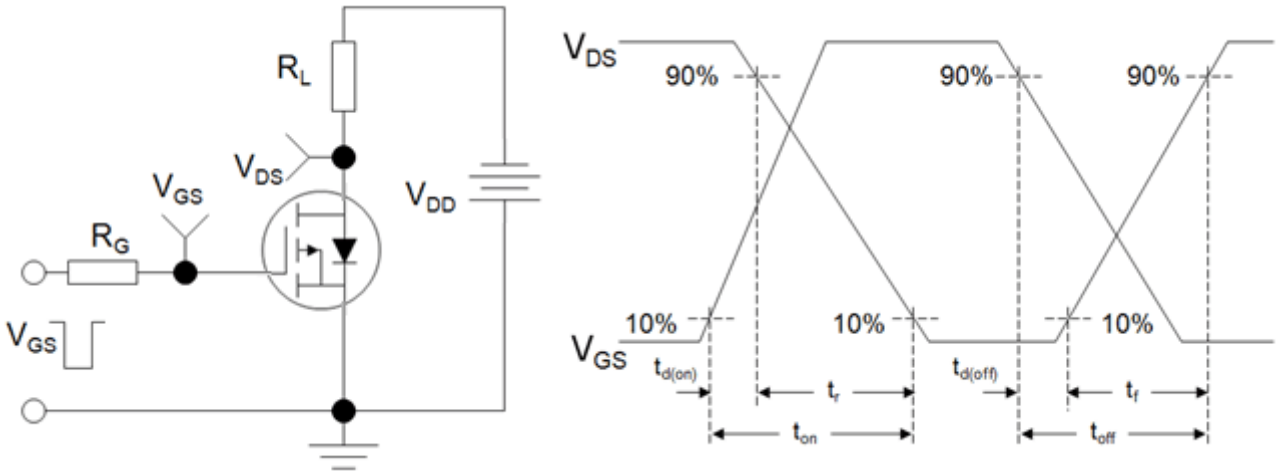
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G
3. V_{DD} = -30V, R_G = 25Ω, L=0.5 mH, Starting T_J = 25°C 。

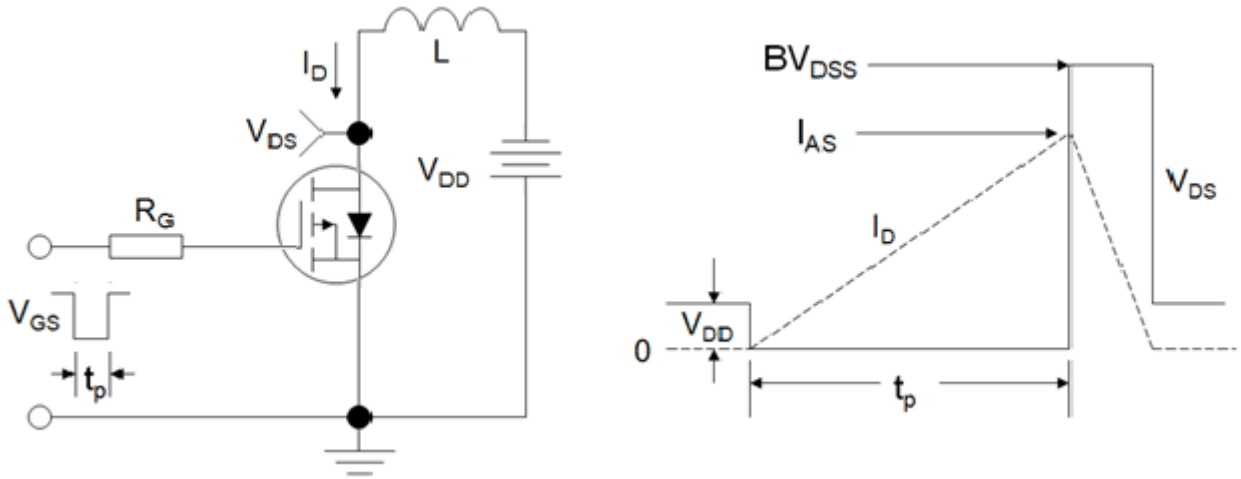
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

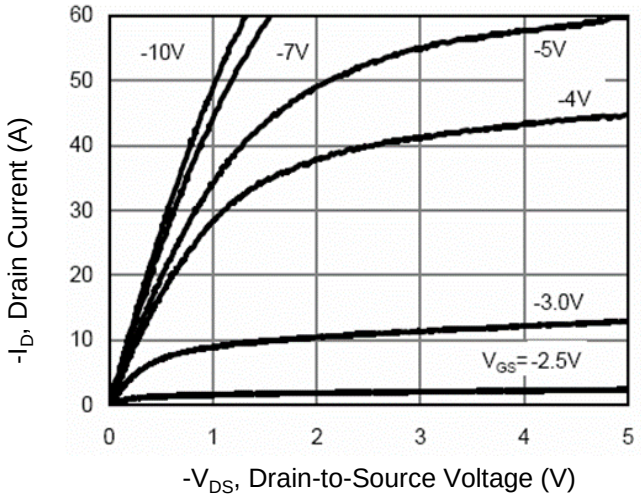


Figure 2. Transfer Characteristics

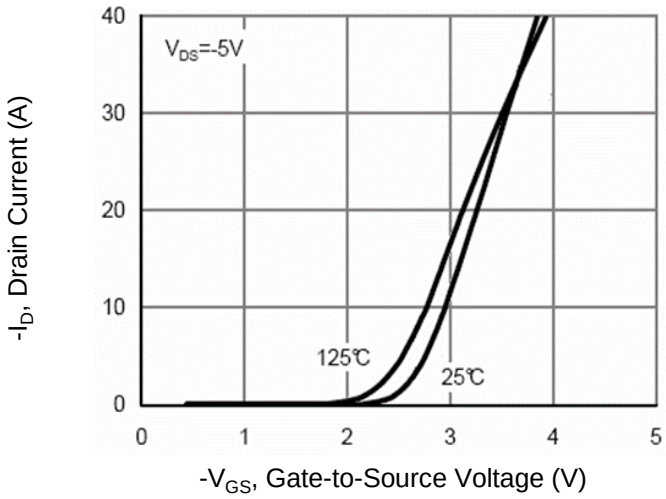


Figure 3.Rdson vs Vgs

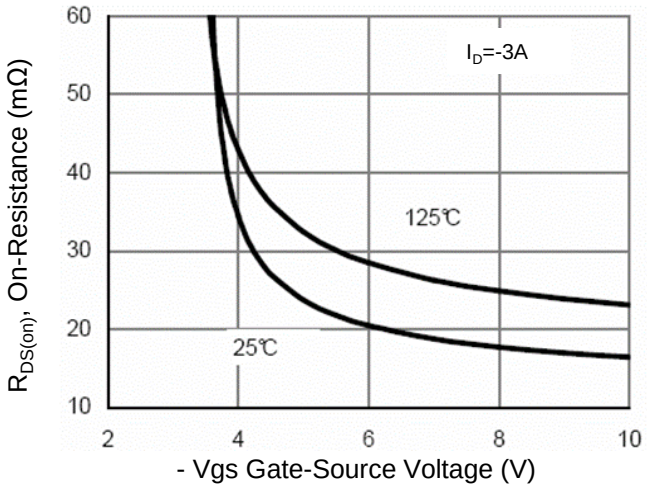


Figure 4. Gate Charge

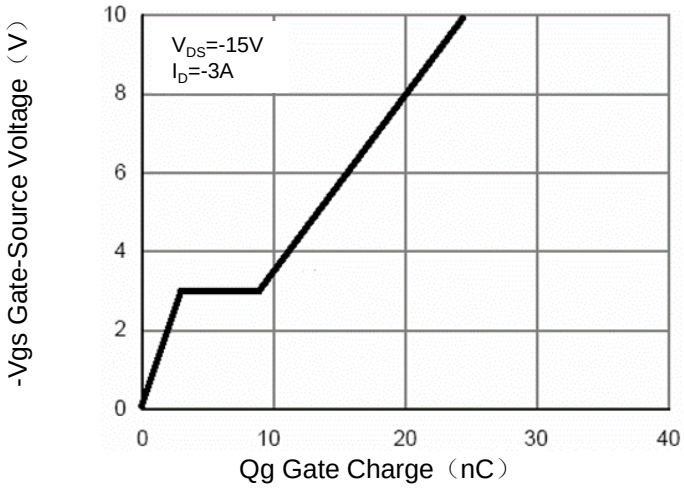


Figure 5. Capacitance vs Vds

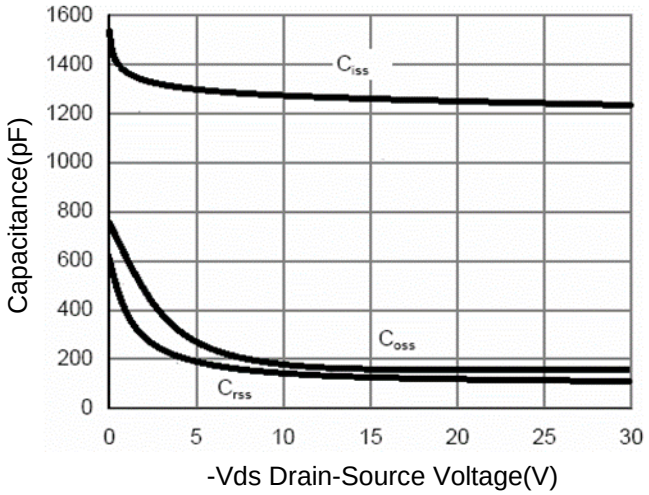
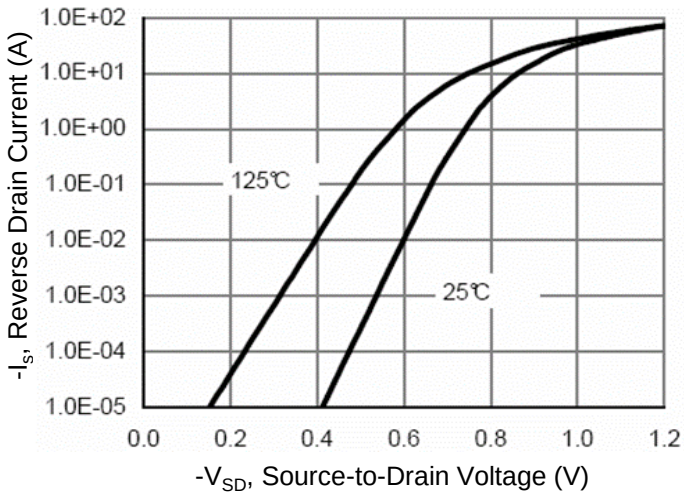


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

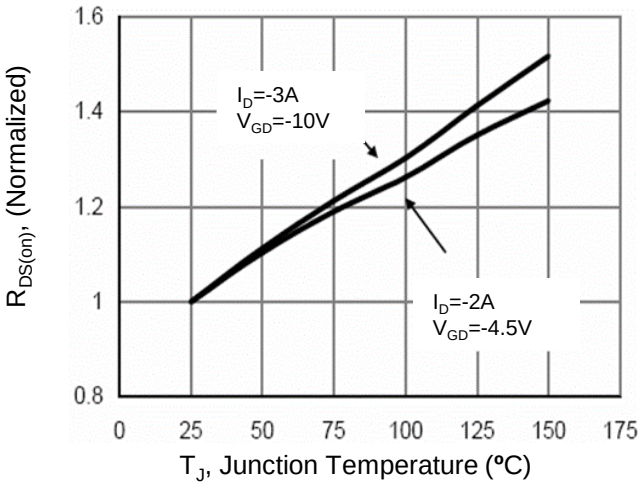


Figure 10. Safe Operation Area

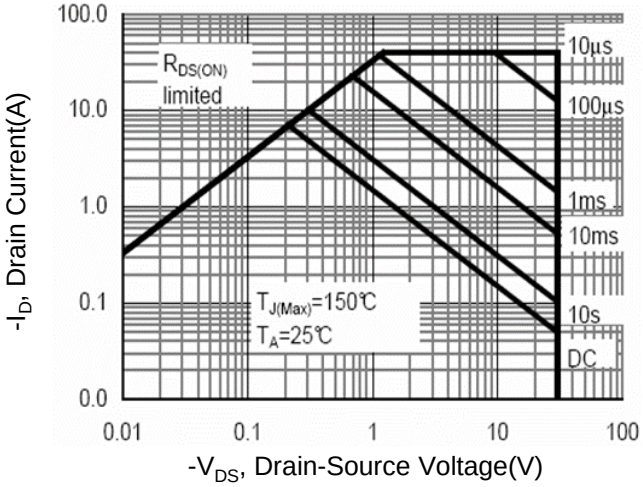


Figure 9. Normalized Maximum Transient Thermal Impedance